ELECTRONICS, INC.
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NTE2652 (PNP) & NTE2653 (NPN)
Silicon Complementary Transistors
High Current Driver

Features:
- Low Saturation Voltage
- Large Current Capacity and Wide ASO

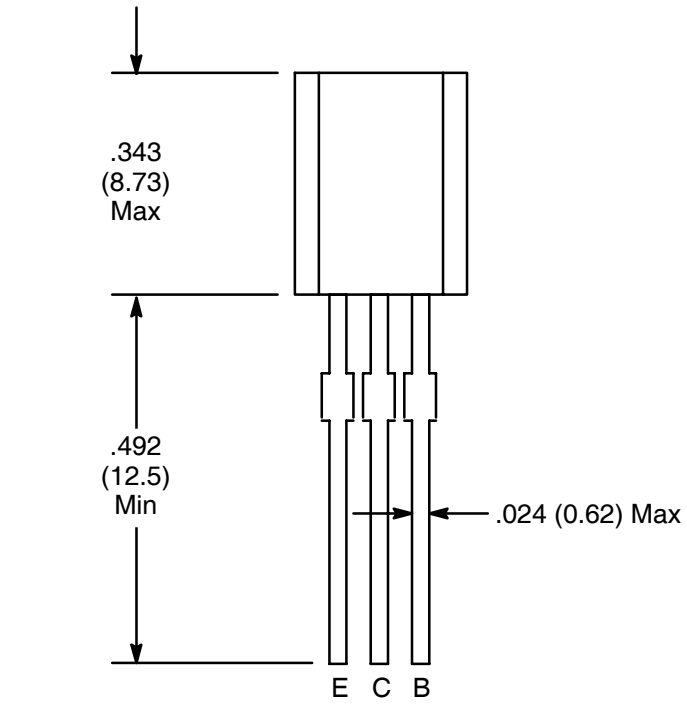
Applications:
- Power Supplies
- Relay Drivers
- Lamp Drivers
- Electrical Equipment

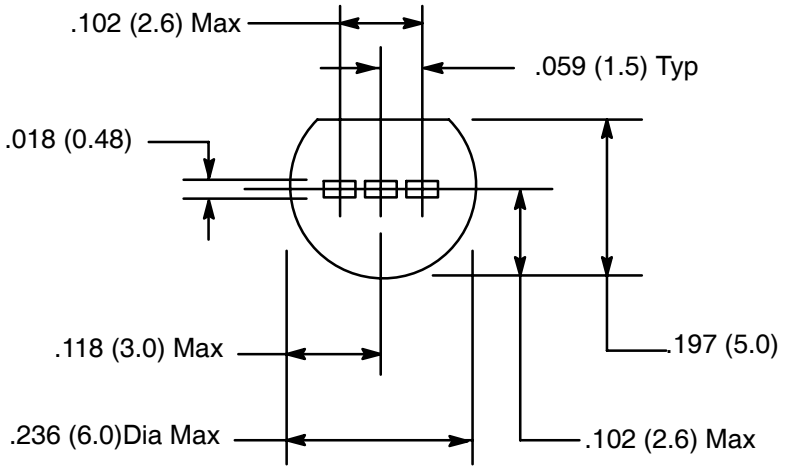
Absolute Maximum Ratings: (T_A = +25°C unless otherwise specified)

Collector–Base Voltage, V_{CBO} 60V
Collector–Emitter Voltage, V_{CEO} 50V
Emitter–Base Voltage, V_{EBO} 6V
Collector Current, I_C
  Continuous 3A
  Pulsed 6A
Collector Dissipation, P_C 1W
Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	V_{CBO}	V_{CB} = 40V, I_E = 0	–	–	1.0	μA
Emitter Cutoff Current	V_{EBO}	V_{EB} = 4V, I_C = 0	–	–	1.0	μA
DC Current Gain	h_{FE}	V_{CE} = 2V, I_C = 100mA	140	–	560	
		V_{CE} = 2V, I_C = 3A	–	40	–	
Gain–Bandwidth Product	f_T	V_{CE} = 10V, I_C = 50mA	–	150	–	MHz
Output Capacitance	c_{ob}	V_{CB} = 10V, f = 1MHz	–	25	–	pF
Collector to Emitter Saturation Voltage NTE2652	$V_{CE(sat)}$	I_C = 2A, I_B = 100mA	–	0.19	0.5	V
NTE2653			–	0.35	0.7	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 2A, I_B = 100mA	–	0.94	1.2	V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = 10μA, I_E = 0	60	–	–	V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 1mA, R_{BE} = ∞	50	–	–	V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = 10μA, I_C = 0	6	–	–	V


.343
(8.73)
Max
.492
(12.5)
Min
.024 (0.62) Max
E C B


.102 (2.6) Max
.059 (1.5) Typ
.018 (0.48)
.118 (3.0) Max
.197 (5.0)
.236 (6.0)Dia Max
.102 (2.6) Max